IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.:

Unknown

Confirmation No.:

Unknown

First Named Inventor:

Constantin Bulucea

Filing Date:

Herewith

Group Art Unit:

Unknown

Examiner:

Unknown

Division of U.S. parent application 10/054,653 filed 18 January 2002

Atty. Docket No.:

NS-5127-1D US

Title:

Gate-Enhanced Junction Varactor With Gradual Capacitance

Variation

Assignee:

National Semiconductor Corporation

Mountain View, California 31 October 2003

Appl'n No.: Unknown

MAIL STOP PATENT APPLICATION COMMISSIONER FOR PATENTS PO Box 1450 Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

Pursuant to 37 CFR 1.56, 1.97, and 1.98, the documents listed on the accompanying substitute PTO Form 1449 are called to the attention of the Examiner for the above patent application. The listed documents include Bulucea, U.S. patent application 09/903,059, filed 10 July 2001. A copy of each of these documents is enclosed. Further enclosed is a copy of an English abstract of each of Japanese Patent Publications 6-61446 and 7-226643.

All of the preceding documents were cited in U.S. application 09/903,059 or/and in the General Disclosure-of-the-Invention section of the present application.

U.S. application 09/903,059, now pending, was published after the 18 January 2002 filing date of U.S. patent application 10/057,653, the parent of the present application. Application 09/903,059 has the same inventorship as the present application and is assigned to the same assignee as the present application. As far as Applicant's Attorney can determine, application 09/903,059 is not prior art to the present application.

Citation of the above documents shall not be construed as:

- 1. an admission that the documents are necessarily prior art with respect to the instant invention;
- 2. a representation that a search has been made; or
- 3. an admission that the information cited herein is, or is considered to be, material to patentability as defined in 37 CFR 1.56(b).

Please call Applicant's Attorney at 650-964-9797 if you have any questions.

EXPRESS MAIL LABEL NO:

EV 337 115 384 US

Respectfully submitted,

Ronald J. Meetin Attorney for Applicants Reg. No. 29,089

210 Central Avenue Mountain View, CA 94043-4869

Ronald J. Meetin

.S. Department of Commerce, Patent and Trademark Office					Atty Docket No.			Application No.		
						NS-5127-1D US			Unknown	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT						Applicant			Confirmation No	
(Use several sheets if necessary)						Constantin Bulucea			Unknown	
						Filing Date			Group	
						Herewith			Unknown	
			U.S.	Patent Documents						
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(Use several sheets if necessary)						Constantin Bulucea			9448		
						Filing Date			Group		
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